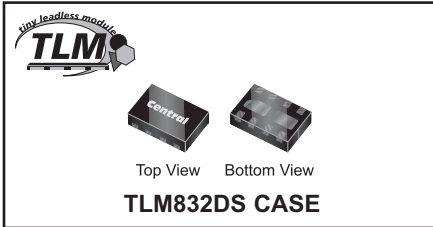


**CTLDM304P-M832DS****SURFACE MOUNT  
DUAL P-CHANNEL  
ENHANCEMENT-MODE  
SILICON MOSFET**

www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CTLDM304P-M832DS is a dual enhancement-mode P-Channel silicon MOSFET designed for high speed pulsed amplifier and driver applications. This energy efficient MOSFET offers beneficially low  $r_{DS(ON)}$ , low gate charge, and low threshold voltage.

**MARKING CODE: C430****APPLICATIONS:**

- Switching circuits
- DC-DC converters
- Power management

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Drain-Source Voltage	
Gate-Source Voltage	
Continuous Drain Current (Steady State)	
Maximum Pulsed Drain Current, $t_p=10\mu\text{s}$	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	

**FEATURES:**

- Low  $r_{DS(ON)}$
- High drain current
- Low gate charge

SYMBOL		UNITS
$V_{DS}$	30	V
$V_{GS}$	12	V
$I_D$	4.2	A
$I_{DM}$	30	A
$P_D$	1.65	W
$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
$\theta_{JA}$	76	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{GSSF}, I_{GSSR}$	$V_{GS}=12\text{V}, V_{DS}=0$			100	nA
$I_{DSS}$	$V_{DS}=24\text{V}, V_{GS}=0$			1.0	$\mu\text{A}$
$BV_{DSS}$	$V_{GS}=0, I_D=250\mu\text{A}$	30			V
$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	0.7	1.0	1.3	V
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=4.2\text{A}$		60	70	$\text{m}\Omega$
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=4.0\text{A}$		64	75	$\text{m}\Omega$
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=1.0\text{A}$		86	120	$\text{m}\Omega$
$Q_g(\text{tot})$	$V_{DS}=15\text{V}, V_{GS}=4.5\text{V}, I_D=4.0\text{A}$		6.4		nC
$Q_{gs}$	$V_{DS}=15\text{V}, V_{GS}=4.5\text{V}, I_D=4.0\text{A}$		1.8		nC
$Q_{gd}$	$V_{DS}=15\text{V}, V_{GS}=4.5\text{V}, I_D=4.0\text{A}$		1.4		nC
$C_{rss}$	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		53		pF
$C_{iss}$	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		760		pF
$C_{oss}$	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		50		pF
$t_{on}$	$V_{DD}=15\text{V}, V_{GS}=10\text{V}, I_D=1.0\text{A}$ $R_L=3.6\Omega, R_G=6.0\Omega$		40		ns
$t_{off}$	$V_{DD}=15\text{V}, V_{GS}=10\text{V}, I_D=1.0\text{A}$ $R_L=3.6\Omega, R_G=6.0\Omega$		75		ns

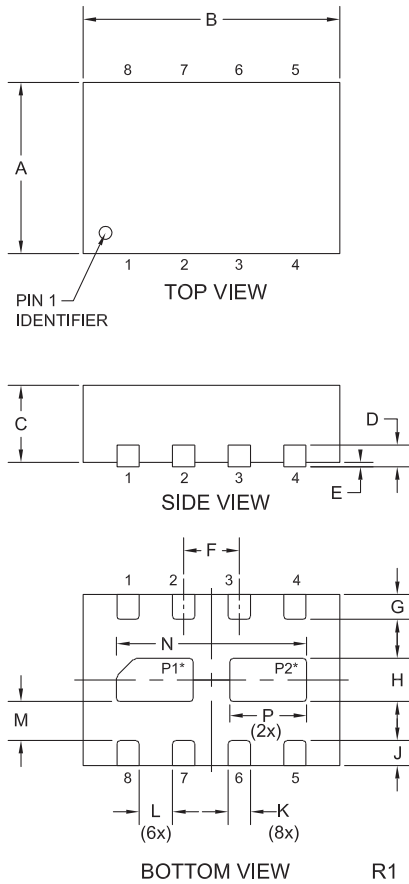
R1 (9-October 2012)

CTLDM304P-M832DS

**SURFACE MOUNT  
DUAL P-CHANNEL  
ENHANCEMENT-MODE  
SILICON MOSFET**



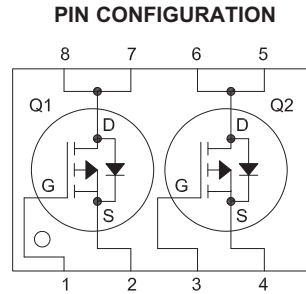
**TLM832DS CASE - MECHANICAL OUTLINE**



\* Exposed pad P1 common to pins 7 and 8  
Exposed pad P2 common to pins 5 and 6

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.077	0.081	1.95	2.05
B	0.116	0.120	2.95	3.05
C	0.031	0.039	0.80	1.00
D	0.006	0.010	0.16	0.25
E	0.000	0.002	0.00	0.05
F	0.026		0.65	
G	0.008	0.016	0.19	0.40
H	0.014	0.024	0.35	0.61
J	0.008	0.016	0.19	0.40
K	0.008	0.012	0.21	0.31
L	0.013	0.017	0.34	0.44
M	0.006	—	0.15	—
N	0.087		2.22	
P	0.029	0.039	0.74	1.00

TLM832DS (REV:R1)



**LEAD CODE:**

- 1) Gate Q1
- 2) Source Q1
- 3) Gate Q2
- 4) Source Q2
- 5) Drain Q2
- 6) Drain Q1
- 7) Drain Q1
- 8) Drain Q1

**MARKING CODE: C430**

R1 (9-October 2012)